

Doc. No.: 2222002 Issue date: September 1, 2022

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High Power Devices Division Power Discrete Business Headquarters ROHM Co., Ltd.

Notification of Product/Process Change

This is an announcement of change(s) to the process of the products currently supplied by ROHM Co., Ltd.

We request your acknowledgement of the receipt of this notification within the given period.

Please provide	e your reply by Sep	tember 1,	2023					
Title of change	Wafer Diameter Change, Wafer Process Production Site Change for 3rd Generation SiC MOSFET (TO247N Package) SCT3****L Series [PCN No.2222002]							
Affected product(s)	Manufacturer part number				Customer part number			
	SCT3 D D LGC11/SCT3 D D LHRC11							
	Now				After			
Detailed description of change	On-board SiC chip's wafer diameter:4inch Front-end manufacturing plants ROHM Apollo Co., Ltd. Chikugo Plant				•On-board SiC chip's wafer diameter:6inch •Front-end manufacturing plants : Lapis Semiconductor Co., Ltd. Miyazaki Plant			
Reason for change	To expand production capacity.							
Anticipated impact on quality	There is no difference in reliability and electrical characteristics.							
Identification of change	It can be identified by Lot number.							
Planned first ship date : April 1, 2023				Sample av	ample available schedule: Within 1.5 months from request			
Attachements (data, report)		yes	s 4M 2222002-2_4		ME RIbl	2222002-3_Rlbl		
Comments								
				Donk	, data			
	Reply date							
Customer reply	1. Approved. 2. Accepted with conditions. 3. Rejected.							
Condition for appr	roval / reason for re	jection						
Comments								
Customer compan	y name							
Customer signature D				Departn	tment			
Customer signature				Departn	partment			